

GUJARAT TECHNOLOGICAL UNIVERSITY**BE- SEMESTER-VI (NEW) EXAMINATION – WINTER 2020****Subject Code:2161101****Date:29/01/2021****Subject Name:VLSI Technology & Design****Time:02:00 PM TO 04:00 PM****Total Marks: 56****Instructions:**

1. Attempt any FOUR questions out of EIGHT questions.
2. Make suitable assumptions wherever necessary.
3. Figures to the right indicate full marks.

		MARKS
Q.1	(a) Compare Semi-custom and Full custom VLSI design style	03
	(b) Draw voltage transfer characteristics of inverter and define V_{IL} , V_{IH} , V_{OL} , V_{OH} , NM_L and NM_H .	04
	(c) Explain the VLSI design flow.	07
Q.2	(a) Write advantages and disadvantages of dynamic logic circuit.	03
	(b) Realize following Boolean logic equation using CMOS inverter. $Z = (AB + C(D+E))'$	04
	(c) Derive the drain current equation for MOSFET using Gradual Channel Approximation (GCA).	07
Q.3	(a) Which are the four general criteria to measure design quality of a fabricated integrated circuit (chip)?	03
	(b) Draw resistive load inverter. Derive V_{IL} and V_{IH} critical voltage equation of resistive load inverter.	04
	(c) Design a resistive-load inverter with $R = 1 \text{ k}\Omega$, such that $V_{OL} = 0.6 \text{ V}$. The enhancement-type nMOS driver transistor has the following parameters $V_{DD} = 5.0 \text{ V}$, $V_{TO} = 1.0 \text{ V}$, $\mu_n C_{ox} = 22.0 \mu\text{A/V}^2$ (a) Determine the required aspect ratio, W/L . (b) Determine V_{IL} and V_{IH} . (c) Determine noise margins NM_L and NM_H .	07
Q.4	(a) Write advantage and disadvantage of both the enhancement load inverter configuration.	03
	(b) Draw CMOS inverter with label name of pMOS and nMOS. Derive V_{IL} critical Voltage equation of CMOS inverter.	04
	(c) Consider a CMOS inverter circuit with the following parameters: $V_{DD} = 3.3 \text{ V}$, $V_{TON} = 0.6 \text{ V}$, $V_{TOP} = -0.7 \text{ V}$, $k_n = 200 \mu\text{A/V}^2$, $k_p = 80 \mu\text{A/V}^2$, find the NM_L .	07
Q.5	(a) What is the need of Scaling? Mention the merits and demerits of constant voltage scaling.	03
	(b) Draw tristate input circuit using Transmission Gate and CMOS inverter and also write its truth table.	04
	(c) Draw circuit for CMOS two input NOR gate. Derive V_{TH} of the same.	07
Q.6	(a) Draw CMOS implementation of D latch with two inverters and two CMOS TG gates.	03

(b) Implement following Boolean logic equation using Transmission Gate (TG). 04

$$Y = AB + A'C' + AB'C$$

(c) What is the need for voltage bootstrapping? Explain dynamic voltage bootstrapping circuit with necessary mathematical analysis. 07

Q.7 (a) Draw general structure of scan based design. 03

(b) Give comparison between FPGA and CPLD. 04

(c) Write a short note on CMOS Transmission gate. 07

Q.8 (a) Define and discuss Latch-up problem in CMOS inverter. 03

(b) Find a equivalent CMOS inverter circuit for simultaneous switching of all inputs, assume that $(W/L)_p = 15$ for all pMOS transistors and $(W/L)_n = 10$ for all nMOS transistors for the following Boolean equation $F = [(C+D+E) \cdot (B+A)]'$ 04

(c) Discuss the on-chip clock generation and distribution. 07

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